N-Channel 250-V (D-S) MOSFET

Key Features:

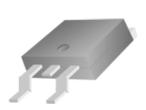
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

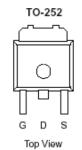
Typical	l Applica	ations:
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- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)		
250	1100 @ V _{GS} = 10V	5.6		







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Limit	Units	
Drain-Source Voltage		V_{DS}	250	V	
Gate-Source Voltage			±20	V	
Continuous Drain Current a	T _C =25°C	I_D	5.6	Α	
Pulsed Drain Current ^b		I _{DM}	20	^	
Continuous Source Current (Diode Conduction) ^a			6	Α	
Power Dissipation ^a	T _C =25°C	P_D	50	W	
Operating Junction and Storage Temperature Range		T_J,T_stg	-55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient ^a	$R_{\theta JA}$	40	°C/W		
Maximum Junction-to-Case	$R_{\theta JC}$	3	C/VV		

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

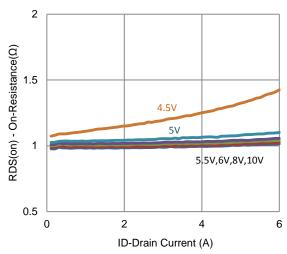
Parameter	Symbol	nbol Test Conditions		Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	l	$V_{DS} = 200 \text{ V}, V_{GS} = 0 \text{ V}$	1		1	uA	
Zero Gate Voltage Brain Gurrent	I _{DSS}	$V_{DS} = 200 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	8.5			Α	
Drain-Source On-Resistance a	r _{DS(on)}	$V_{GS} = 10 \text{ V}, I_{D} = 2 \text{ A}$			1000	mΩ	
Forward Transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 2 \text{ A}$		9		S	
Diode Forward Voltage ^a	V_{SD}	$I_{S} = 3 \text{ A}, V_{GS} = 0 \text{ V}$		0.74		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = 100 \text{ V}, V_{GS} = 10 \text{ V},$		8.8			
Gate-Source Charge	Q_gs	$I_D = 2 A$		2.0		nC	
Gate-Drain Charge	Q_gd	1D - 271		2.2			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 100 \text{ V}, R_{L} = 50 \Omega,$		6			
Rise Time	t _r	$I_{DS} = 100 \text{ V}, \text{ KL} = 30 \Omega_2,$ $I_{D} = 2 \text{ A},$		4		ns	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		19		113	
Fall Time	t _f	VGEN - 10 V, NGEN 0 12		9			
Input Capacitance	C _{iss}			610			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		44		pF	
Reverse Transfer Capacitance	C_{rss}			30			

Notes

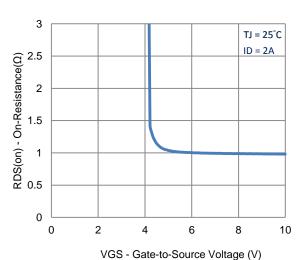
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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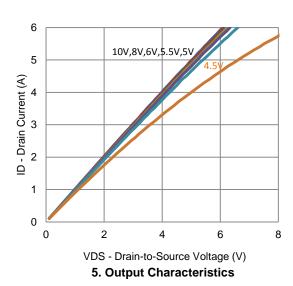
Typical Electrical Characteristics

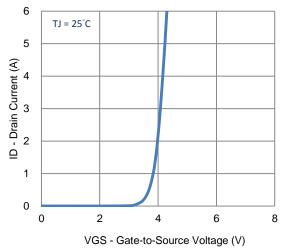


1. On-Resistance vs. Drain Current

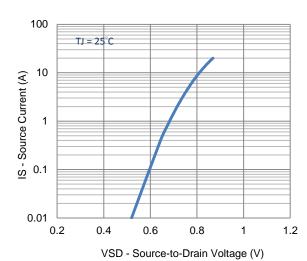


3. On-Resistance vs. Gate-to-Source Voltage

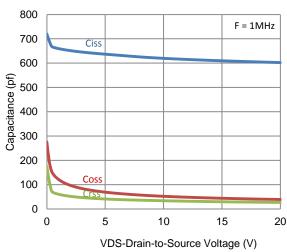




2. Transfer Characteristics

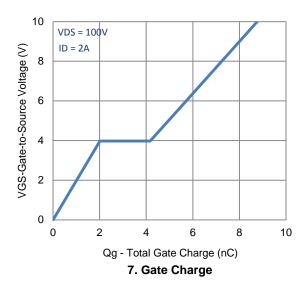


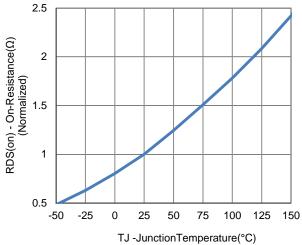
4. Drain-to-Source Forward Voltage

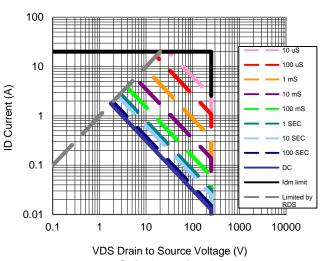


6. Capacitance

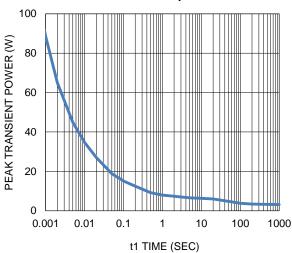
Typical Electrical Characteristics





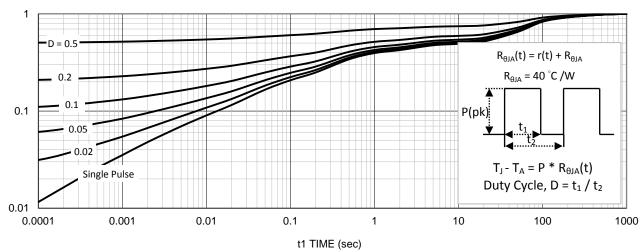






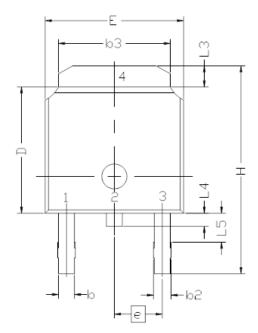
9. Safe Operating Area

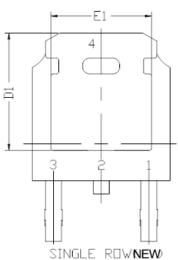
10. Single Pulse Maximum Power Dissipation

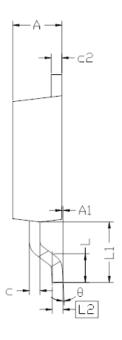


11. Normalized Thermal Transient Junction to Ambient

Package Information







CVADDI	DIMENS:	[DNAL F	REQMTS
SYMBOL	MIN	NDM	MAX
E	6.40	6.60	6.731
L	1.40	1.52	1.77
L1		.743 RI	
	0.	.508 BS	
L3	0.89		1.27
L4	0.64		1.01
L5			
D	6.00	6.10	6.223
Н	9.40	10.00	10.40
b	0.64	0.76	0,88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
е	2.	286 BS	C
Α	2.20	2.30	2,38
A1	0		0.127
	0.45	0.50	0.60
c2	0.45	0.50	0,58
D1	5,30		
E1	4.40		
θ	0°		10°

Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.